

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	0	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near lead) and package and encapsula\$6 and wire and leadframe and (257/687. ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 09:40
S1	26	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and ground and wire and encapsulant and polyimide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:58
S2	24	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and ground and wire and encapsulant and polyimide and insulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 12:08
S3	24	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and ground and wire and encapsulant and polyimide and insulat\$4 and plat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 12:09
S4	24	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and ground and wire and encapsulant and polyimide and insulat\$4 and plat\$4 and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:58
S5	0	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and (ground near wire) and encapsula\$8 and polyimide and insulat\$4 and plat\$4 and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 11:56
S6	17	(heat near sink) and (semiconductor or die or wafer) and lead\$2 and electrical\$4 and ground and wire and encapsulant and polyimide and insulat\$4 and plat\$4 and package and ring	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/23 10:58
S7	0	((heat near sink) near4 (semiconductor or die or wafer)) and (plurality near4 lead\$2) and electrical\$4 and (ground near4 lead) and wire and encapsulant and polyimide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:45

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S8	25	((heat near sink) near4 (semiconductor or die or wafer)) and (plurality near4 lead\$2) and electrical\$4 and (ground near4 lead) and wire and encapsulant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:46
S9	0	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near4 lead) and electrical\$4 and ground and wire and encapsulant and polyimide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 14:59
S10	709	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near4 lead)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:00
S11	209	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near4 lead) and package and encapsula\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:01
S12	181	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near4 lead) and package and encapsula\$6 and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:04
S13	48	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near4 lead) and package and encapsula\$6 and wire and leadframe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:05
S14	31	(heat near sink) and (semiconductor or die or wafer or substrate) and (ground near lead) and package and encapsula\$6 and wire and leadframe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/19 09:40